L Number	Hits	Search Text	DB	Time stamp
8	593	('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry with	USPAT;	2003/09/09 07:45
		water)	US-PGPUB;	
			ЕРО; ЈРО	
9	587	(('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT;	2003/09/09 07:40
		with water)) and polish\$3	US-PGPUB;	
		•	ЕРО; ЈРО	
10	587	((('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT;	2003/09/09 07:41
		with water)) and polish\$3) and water	US-PGPUB;	
		,, ,	ЕРО; ЛРО	
11	208	(((('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT;	2003/09/09 07:41
		with water)) and polish\$3) and water) and dilut\$3	US-PGPUB,	
			ЕРО: ЛРО	
12	207	((((('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT;	2003/09/09 07:42
		with water)) and polish\$3) and water) and dilut\$3) and (wafer substrate	US-PGPUB;	
		workpiece)	ЕРО; ЛРО	
13	128	(((((('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT:	2003/09/09 07:58
		with water)) and polish\$3) and water) and dilut\$3) and (wafer substrate	US-PGPUB:	
		workpiece)) and polishing adj slurry	ЕРО; ЛРО	
14	54	((((((('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT;	2003/09/09 07:42
		with water)) and polish\$3) and water) and dilut\$3) and (wafer substrate	US-PGPUB;	
		workpiece)) and polishing adj slurry) and (slurry with dispersion)	ЕРО; ЛРО	
15	53	((((((('('CMP' '(CMP)' chemical adj mechanical adj polishing) with	USPAT:	2003/09/09 07:45
	•	(slurry with water)) and polish\$3) and water) and dilut\$3) and (wafer	US-PGPUB;	
		substrate workpiece)) and polishing adj slurry) and (slurry with	ЕРО; ЛРО	
		dispersion)) and ("CMP" "(CMP)")		
19	62	(((((('CMP' '(CMP)' chemical adj mechanical adj polishing) with (slurry	USPAT:	2003/09/09 07:59
	02	with water)) and polish\$3) and water) and dilut\$3) and (wafer substrate	US-PGPUB;	
		workpiece)) and (polishing adj slurry with silica)	EPO; JPO	
20	38	(((((((('('('('CMP' '(CMP)' chemical adj mechanical adj polishing) with	USPAT;	2003/09/09 07:59
	50	(slurry with water)) and polish\$3) and water) and dilut\$3) and (wafer	US-PGPUB;	
		substrate workpiece)) and polishing adj slurry) and (slurry with	ЕРО; ЛРО	
		dispersion)) and ("CMP" "(CMP)")) and (polishing adj slurry with	1,7,0,310	
		silica)		
21	1	Silica)	USPAT	2003/09/09 08:03